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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
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Complete if Known

Application Number	Unknown 10/788,810
Filing Date	Even Date Herewith 2-27-04
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2825
Examiner Name	Unknown Any

Sheet 1 of 5

Attorney Docket No: 1303.027US2

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Substitute Disclosure Statement Form (PTO-1449)

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Application Number	Unknown 10/88,810
Filing Date	Even Date Here with 2-27-00
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2825
Examiner Name	Unknown Amy a

Sheet 2 of 5

Attorney Docket No: 1303.027US2

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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Application Number	Unknown 10/788,810
Filing Date	Even Date Herewith 2-22-04
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2825
Examiner Name	Unknown Amy M

Sheet 3 of 5

Attorney Docket No: 1303.027US2

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Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) ? Applicant is to place a check mark here if English language Translation is attached

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown <b>6788, 810</b>
	Filing Date	Even Date Herewith <b>2-22-04</b>
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown <b>2825</b>
	Examiner Name	Unknown <b>Any a</b>
Sheet 4 of 5		Attorney Docket No: 1303.027US2

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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EXAMINER

DATE CONSIDERED

**8/4/04**

Substitute Disclosure Statement Form (PTO-1446)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 808. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) Applicant is to place a check mark here if English language Translation is attached

10/788, 810

PTO/SB/08A (10-01)

Approved for use through 10/31/2002, OMB 551-0031

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Application Number	Unknown 10/788, 810
Filing Date	Even Date Herewith 2-27-04
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2825
Examiner Name	Unknown Amy V

Sheet 5 of 5

Attorney Docket No: 1303.027US2

## OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)

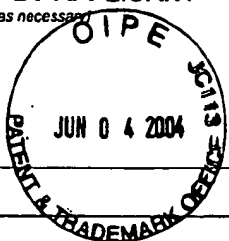
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Application Number	10/788810
Filing Date	February 27, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	<del>2812</del> 2828
Examiner Name	Unknown Any 9

Sheet 1 of 1

Attorney Docket No: 1303.027US2

**US PATENT DOCUMENTS**

Examiner Initial*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
1A	US-6,169,306	01/02/2001	Gardner, Mark I., et al.	257	310	07/27/1998

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